

# Epi - Wafer

## n-Type GaN



**Feature** n-Type GaN Epi. Wafer  
Single side polished (Growth surface)

**Diameter** 2" (50.8mm)

**Thickness (Included substrate)** 430 $\mu$ m $\pm$ 15 $\mu$ m

**Structure** n-GaN / u-GaN / Sapphire substrate



GaN on Sapphire Wafer

### Characteristics (at 25°C)

Parameter		Typ.	Test Conditions
PL measurement	Peak wavelength	364nm $\pm$ 1nm	Etamax PLATO - Laser : 213nm
	Uniformity STD	<3%	
	FWHM	<10nm	
	FWHM STD	<3%	
Thickness	Thickness	4 $\mu$ m $\pm$ 10%	
	Thickness STD	<10%	
XRD	(002)	<400 arcsec	Panalytical HRXRD
	(102)	<500 arcsec	
Hall	Carrier Concentration	$\geq 1 \times 10^{18} / \text{cm}^3$	Accent HL5500
	Mobility	$\leq 200 \text{ cm}^2/\text{V}\cdot\text{sec}$	
Doping material	Si	used	-
	Mg	N/A	

### Normalized Single Spectrum(300 ~ 700nm)

